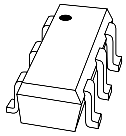


BF1210

Dual N-channel dual gate MOSFET

Rev. 01 — 25 October 2006 **Product data sheet**

1. Product profile

1.1 General description

The BF1210 is a combination of two dual gate MOSFET amplifiers with shared source and gate2 leads.

The source and substrate are interconnected. Internal bias circuits enable DC stabilization and a very good cross modulation performance during AGC. Integrated diodes between the gates and source protect against excessive input voltage surges. The transistor has a SOT363 micro-miniature plastic package.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Two low noise gain controlled amplifiers in a single package; both with a partly integrated bias
- Superior cross modulation performance during AGC
- High forward transfer admittance
- High forward transfer admittance to input capacitance ratio

1.3 Applications

- Gain controlled low noise amplifiers for VHF and UHF applications with 5 V supply voltage
  - digital and analog television tuners
  - professional communication equipment

1.4 Quick reference data

Table 1. Quick reference data

Per MOSFET unless otherwise specified.

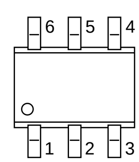
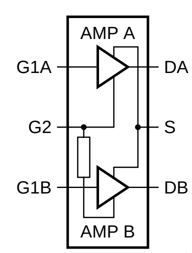
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage			-	-	6	V
I_D	drain current	DC		-	-	30	mA
P_{tot}	total power dissipation	$T_{sp} \leq 107$ °C	[1]	-	-	180	mW
$\|y_{fs}\|$	forward transfer admittance	amplifier A; I_D = 19 mA		26	31	41	mS
		amplifier B; I_D = 13 mA		28	33	43	mS
$C_{iss(G1)}$	input capacitance at gate1	f = 100 MHz	[2]				
		amplifier A		-	2.2	2.7	pF
		amplifier B		-	1.9	2.4	pF
C_{rss}	reverse transfer capacitance	f = 100 MHz	[2]	-	20	-	fF
NF	noise figure	amplifier A; f = 400 MHz		-	0.9	1.5	dB
		amplifier B; f = 800 MHz		-	1.2	1.9	dB
Xmod	cross modulation	input level for k = 1 % at 40 dB AGC					
		amplifier A		100	105	-	dBμV
		amplifier B		100	103	-	dBμV
T_j	junction temperature			-	-	150	°C

[1] T_{sp} is the temperature at the soldering point of the source lead.

[2] Calculated from S-parameters.

2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	gate1 (AMP A)		
2	gate2		
3	gate1 (AMP B)		
4	drain (AMP B)		
5	source		
6	drain (AMP A)		

sym119

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BF1210	-	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking

Type number	Marking	Description
BF1210	*AB	* = p : made in Hong Kong
		* = t : made in Malaysia
		* = w : made in China

5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per MOSFET					
V_{DS}	drain-source voltage		-	6	V
I_D	drain current	DC	-	30	mA
I_{G1}	gate1 current		-	±10	mA
I_{G2}	gate2 current		-	±10	mA
P_{tot}	total power dissipation	$T_{sp} \leq 107$ °C [1]	-	180	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	150	°C

[1] T_{sp} is the temperature at the soldering point of the source lead.

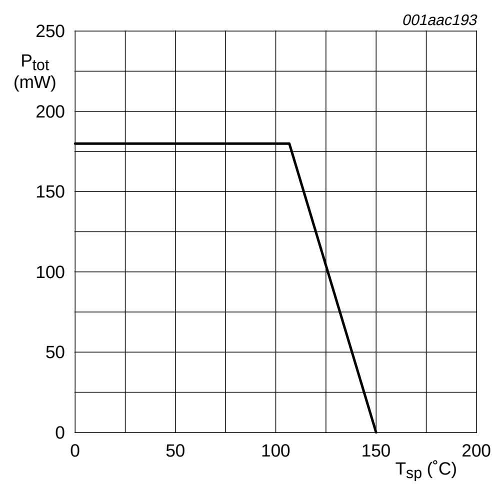


Fig 1. Power derating curve

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		240	K/W

7. Static characteristics

Table 7. Static characteristics
$T_j = 25\,°C$.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per MOSFET; unless otherwise specified							
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{G1-S} = V_{G2-S} = 0$ V; $I_D = 10$ µA					
		amplifier A		6	-	-	V
		amplifier B		6	-	-	V
$V_{(BR)G1-SS}$	gate1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$ V; $I_{G1-S} = 10$ mA		6	-	10	V
$V_{(BR)G2-SS}$	gate2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$ V; $I_{G2-S} = 10$ mA		6	-	10	V
$V_{F(S-G1)}$	forward source-gate1 voltage	$V_{G2-S} = V_{DS} = 0$ V; $I_{S-G1} = 10$ mA		0.5	-	1.5	V
$V_{F(S-G2)}$	forward source-gate2 voltage	$V_{G1-S} = V_{DS} = 0$ V; $I_{S-G2} = 10$ mA		0.5	-	1.5	V
$V_{G1-S(th)}$	gate1-source threshold voltage	$V_{DS} = 5$ V; $V_{G2-S} = 4$ V; $I_D = 100$ µA		0.3	-	1.0	V
$V_{G2-S(th)}$	gate2-source threshold voltage	$V_{DS} = 5$ V; $V_{G1-S} = 5$ V; $I_D = 100$ µA		0.4	-	1.0	V
I_{DS}	drain-source current	$V_{G2-S} = 4$ V	[1]				
		amplifier A; $V_{DS(A)} = 5$ V; $R_{G1(A)} = 59$ kΩ		14	-	24	mA
		amplifier B; $V_{DS(B)} = 5$ V; $R_{G1(B)} = 150$ kΩ		9	-	17	mA
I_{G1-S}	gate1 cut-off current	$V_{G2-S} = 0$ V; $V_{DS(A)} = V_{DS(B)} = 0$ V					
		amplifier A; $V_{G1-S(A)} = 5$ V		-	-	50	nA
		amplifier B; $V_{G1-S(B)} = 5$ V		-	-	50	nA
I_{G2-S}	gate2 cut-off current	$V_{G2-S} = 4$ V; $V_{DS(A)} = V_{DS(B)} = 0$ V; $V_{G1-S(A)} = V_{G1-S(B)} = 0$ V		-	-	20	nA

[1] R_{G1} connects gate1 to $V_{GG} = 5$ V. See Figure 32.

8. Dynamic characteristics

8.1 Dynamic characteristics for amplifier A

Table 8. Dynamic characteristics for amplifier A
Common source; $T_{amb} = 25\,°C$; $V_{G2-S} = 4$ V; $V_{DS(A)} = 5$ V; $I_{D(A)} = 19$ mA.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$\|y_{fs}\|$	forward transfer admittance	$T_j = 25$ °C		26	31	41	mS
$C_{iss(G1)}$	input capacitance at gate1	f = 100 MHz	[1]	-	2.2	2.7	pF
$C_{iss(G2)}$	input capacitance at gate2	f = 100 MHz	[1]	-	3.0	-	pF
C_{oss}	output capacitance	f = 100 MHz	[1]	-	0.9	-	pF
C_{rss}	reverse transfer capacitance	f = 100 MHz	[1]	-	20	-	fF

Table 8. Dynamic characteristics for amplifier A *...continued*

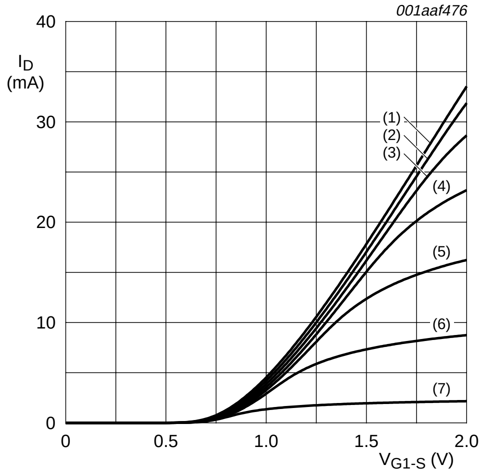
Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; $V_{DS(A)}$ = 5 V; $I_{D(A)}$ = 19 mA.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
G_{tr}	transducer power gain	$B_S = B_{S(opt)}$; $B_L = B_{L(opt)}$	[1]				
		f = 200 MHz; G_S = 2 mS; G_L = 0.5 mS		31	35	39	dB
		f = 400 MHz; G_S = 2 mS; G_L = 1 mS		27	31	35	dB
		f = 800 MHz; G_S = 3.3 mS; G_L = 1 mS		22	26	30	dB
NF	noise figure	f = 11 MHz; G_S = 20 mS; B_S = 0 S		-	3	-	dB
		f = 400 MHz; $Y_S = Y_{S(opt)}$		-	0.9	1.5	dB
		f = 800 MHz; $Y_S = Y_{S(opt)}$		-	1.2	1.9	dB
Xmod	cross modulation	input level for k = 1 %; f_w = 50 MHz; f_{unw} = 60 MHz	[2]				
		at 0 dB AGC		90	-	-	dBμV
		at 10 dB AGC		-	90	-	dBμV
		at 20 dB AGC		-	99	-	dBμV
		at 40 dB AGC		100	105	-	dBμV

[1] Calculated from S-parameters.

[2] Measured in Figure 32 test circuit.

8.1.1 Graphs for amplifier A



(1) V_{G2-S} = 4.0 V.

(2) V_{G2-S} = 3.5 V.

(3) V_{G2-S} = 3.0 V.

(4) V_{G2-S} = 2.5 V.

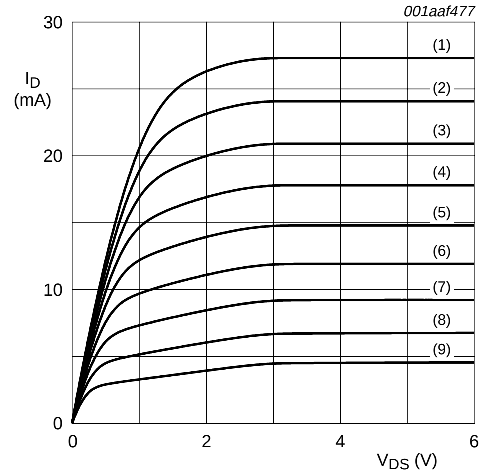
(5) V_{G2-S} = 2.0 V.

(6) V_{G2-S} = 1.5 V.

(7) V_{G2-S} = 1.0 V.

$V_{DS(A)}$ = 5 V; T_j = 25 °C.

Fig 2. Amplifier A: transfer characteristics; typical values



(1) $V_{G1-S(A)}$ = 1.8 V.

(2) $V_{G1-S(A)}$ = 1.7 V.

(3) $V_{G1-S(A)}$ = 1.6 V.

(4) $V_{G1-S(A)}$ = 1.5 V.

(5) $V_{G1-S(A)}$ = 1.4 V.

(6) $V_{G1-S(A)}$ = 1.3 V.

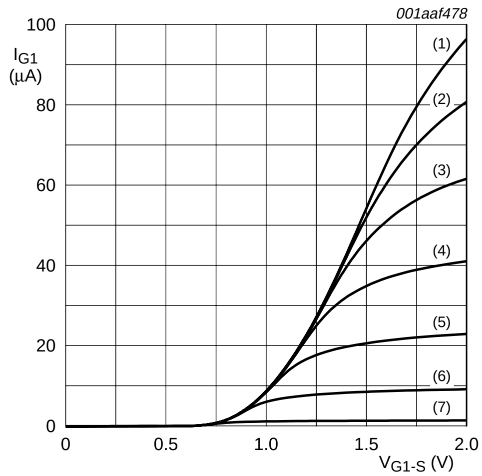
(7) $V_{G1-S(A)}$ = 1.2 V.

(8) $V_{G1-S(A)}$ = 1.1 V.

(9) $V_{G1-S(A)}$ = 1.0 V.

V_{G2-S} = 4 V; T_j = 25 °C.

Fig 3. Amplifier A: output characteristics; typical values



(1) V_{G2-S} = 4.0 V.

(2) V_{G2-S} = 3.5 V.

(3) V_{G2-S} = 3.0 V.

(4) V_{G2-S} = 2.5 V.

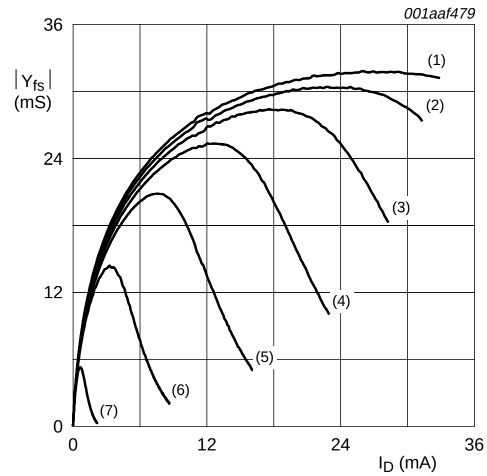
(5) V_{G2-S} = 2.0 V.

(6) V_{G2-S} = 1.5 V.

(7) V_{G2-S} = 1.0 V.

$V_{DS(A)}$ = 5 V; T_j = 25 °C.

Fig 4. Amplifier A: gate1 current as a function of gate1 voltage; typical values



(1) V_{G2-S} = 4.0 V.

(2) V_{G2-S} = 3.5 V.

(3) V_{G2-S} = 3.0 V.

(4) V_{G2-S} = 2.5 V.

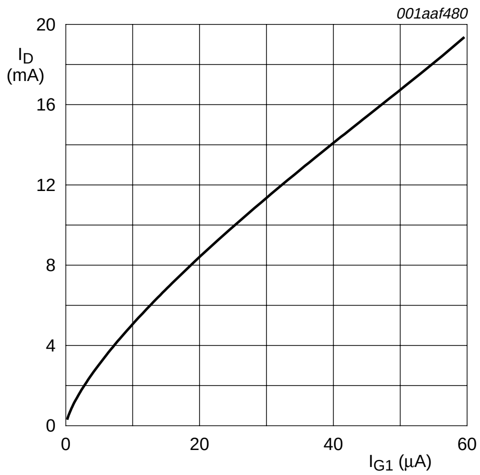
(5) V_{G2-S} = 2.0 V.

(6) V_{G2-S} = 1.5 V.

(7) V_{G2-S} = 1.0 V.

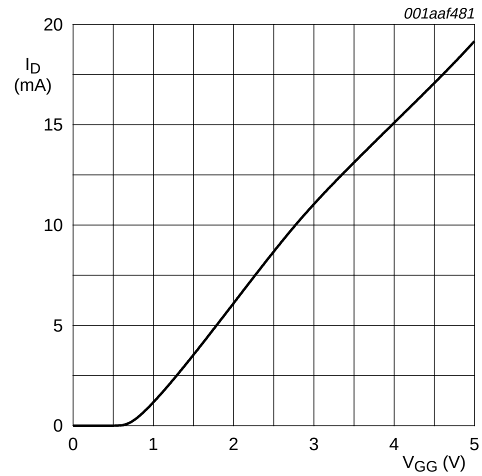
$V_{DS(A)}$ = 5 V; T_j = 25 °C.

Fig 5. Amplifier A: forward transfer admittance as a function of drain current; typical values



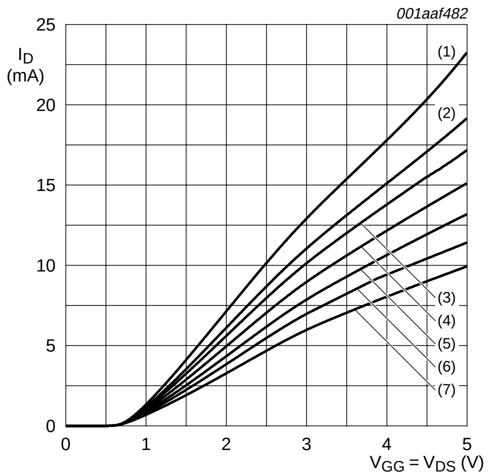
$V_{DS(A)}$ = 5 V; V_{G2-S} = 4 V; T_j = 25 °C.

Fig 6. Amplifier A: drain current as a function of gate1 current; typical values



$V_{DS(A)}$ = 5 V; V_{G2-S} = 4 V; $R_{G1(A)}$ = 59 kΩ; T_j = 25 °C.

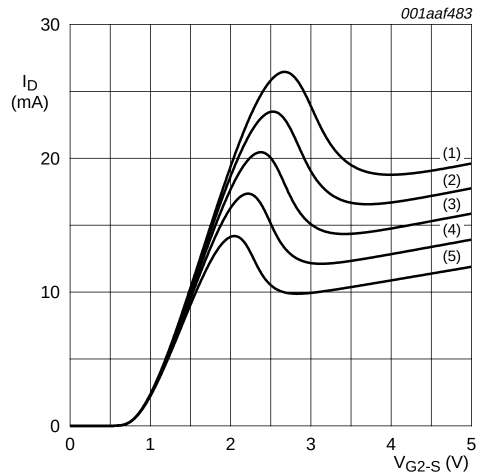
Fig 7. Amplifier A: drain current as a function of gate1 supply voltage (V_{GG}); typical values



(1) $R_{G1(A)} = 47\ k\Omega$.
(2) $R_{G1(A)} = 59\ k\Omega$.
(3) $R_{G1(A)} = 68\ k\Omega$.
(4) $R_{G1(A)} = 82\ k\Omega$.
(5) $R_{G1(A)} = 100\ k\Omega$.
(6) $R_{G1(A)} = 120\ k\Omega$.
(7) $R_{G1(A)} = 150\ k\Omega$.

$V_{G2\text{-}S} = 4$ V; $T_j = 25$ °C.

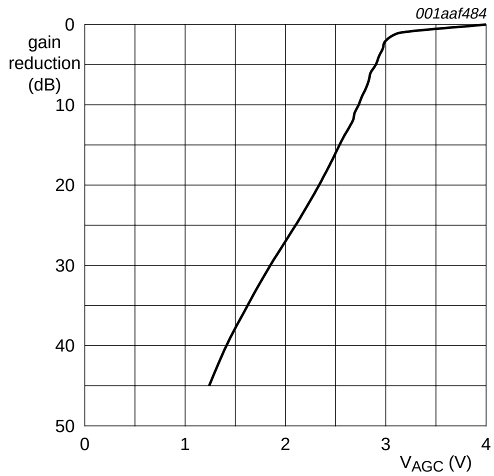
Fig 8. Amplifier A: drain current as a function of V_{DS} and V_{GG}; typical values



(1) $V_{GG} = 5.0$ V.
(2) $V_{GG} = 4.5$ V.
(3) $V_{GG} = 4.0$ V.
(4) $V_{GG} = 3.5$ V.
(5) $V_{GG} = 3.0$ V.

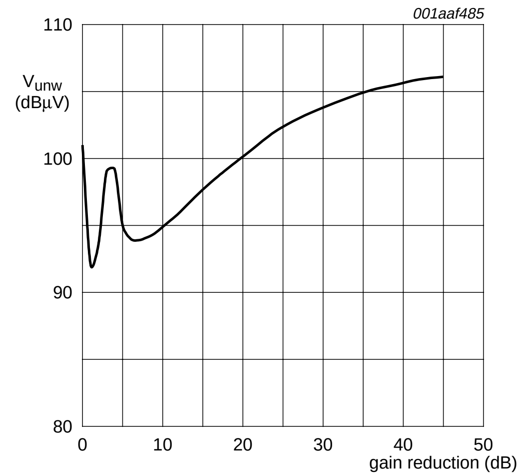
$T_j = 25$ °C; $R_{G1(A)} = 59\ k\Omega$ (connected to V_{GG}).

Fig 9. Amplifier A: drain current as a function of gate2 voltage; typical values



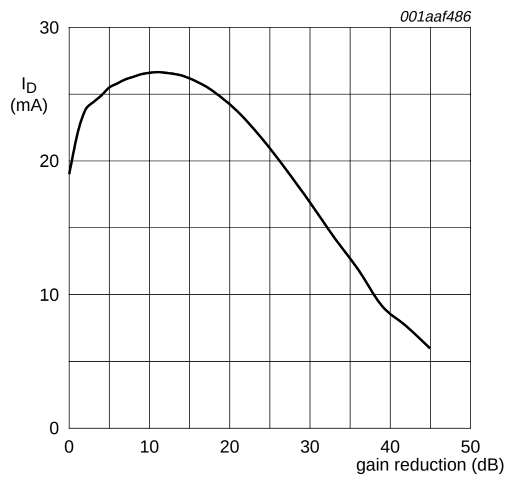
$V_{DS(A)}$ = 5 V; V_{GG} = 5 V; $I_{D(nom)(A)}$ = 19 mA;
$R_{G1(A)}$ = 59 kΩ; f = 50 MHz; T_{amb} = 25 °C;
see Figure 32.

Fig 10. Amplifier A: typical gain reduction as a function of the AGC voltage; typical values



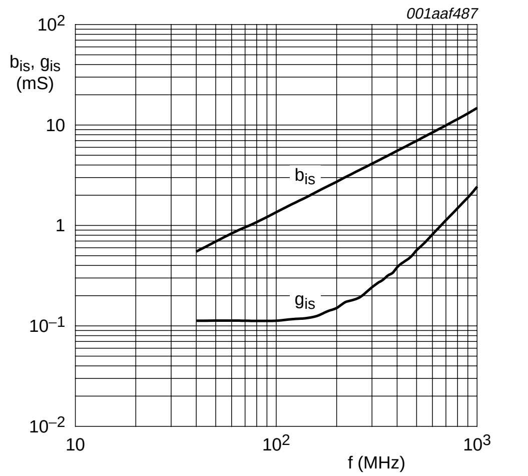
$V_{DS(A)}$ = 5 V; V_{GG} = 5 V; $V_{G2\text{-}S(nom)}$ = 4 V;
$R_{G1(A)}$ = 59 kΩ; f_w = 50 MHz; f_{unw} = 60 MHz;
$I_{D(nom)(A)}$ = 19 mA; T_{amb} = 25 °C; see Figure 32.

Fig 11. Amplifier A: unwanted voltage for 1 % cross modulation as a function of gain reduction; typical values



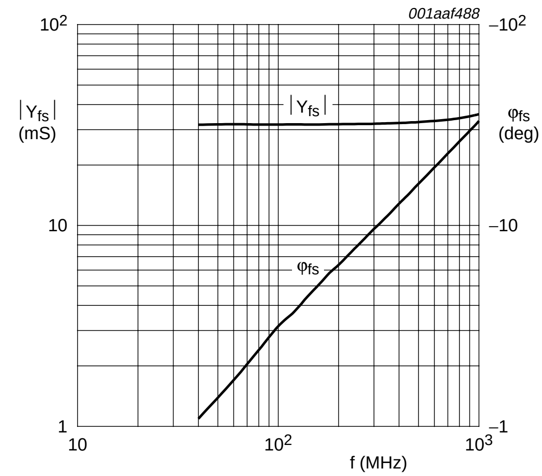
$V_{DS(A)}$ = 5 V; V_{GG} = 5 V; $V_{G2\text{-}S(nom)}$ = 4 V; $R_{G1(A)}$ = 59 kΩ; f = 50 MHz; $I_{D(nom)(A)}$ = 19 mA; T_{amb} = 25 °C; see Figure 32.

Fig 12. Amplifier A: typical drain current as a function of gain reduction; typical values



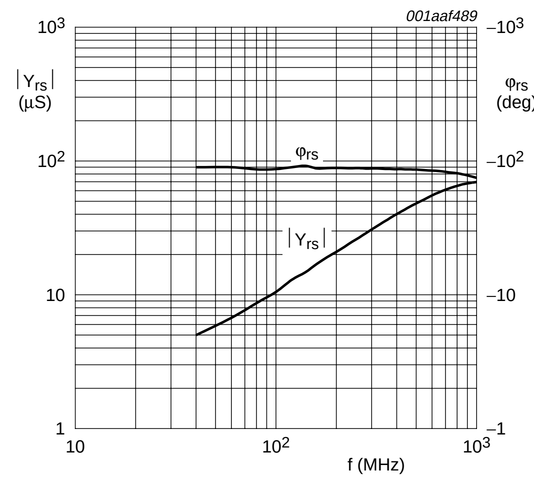
$V_{DS(A)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(B)}$ = 0 V;
$I_{D(A)}$ = 19 mA.

Fig 13. Amplifier A: input admittance as a function of frequency; typical values



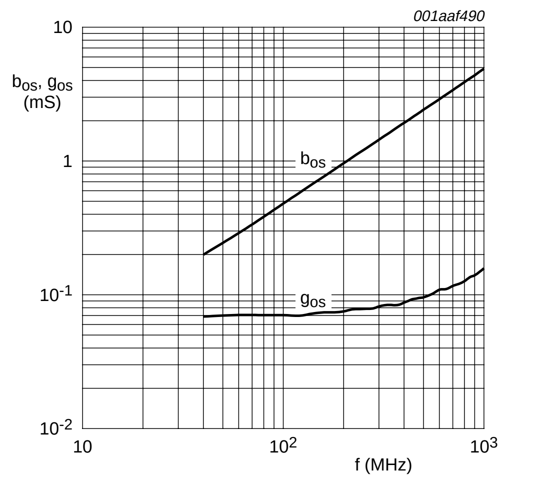
$V_{DS(A)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(B)}$ = 0 V;
$I_{D(A)}$ = 19 mA.

Fig 14. Amplifier A: forward transfer admittance and phase as a function of frequency; typical values



$V_{DS(A)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(B)}$ = 0 V;
$I_{D(A)}$ = 19 mA.

Fig 15. Amplifier A: reverse transfer admittance and phase as a function of frequency; typical values



$V_{DS(A)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(B)}$ = 0 V;
$I_{D(A)}$ = 19 mA.

Fig 16. Amplifier A: output admittance as a function of frequency; typical values

8.1.2 Scattering parameters for amplifier A

Table 9. Scattering parameters for amplifier A

$V_{DS(A)}$ = 5 V; V_{G2-S} = 4 V; $I_{D(A)}$ = 19 mA; $V_{DS(B)}$ = 0 V; $V_{G1-S(B)}$ = 0 V; T_{amb} = 25 °C; typical values.

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)
40	0.9861	–3.2	3.14	176.75	0.00054	87.97	0.9934	–1.19
100	0.9883	–7.84	3.14	171.53	0.00104	87.69	0.9925	–2.85
200	0.9844	–15.7	3.12	163.1	0.00205	80.77	0.9918	–5.69
300	0.9761	–23.52	3.08	154.65	0.00295	76.33	0.9904	–8.51
400	0.9635	–31.26	3.03	146.33	0.00375	72.34	0.9888	–11.33
500	0.9486	–38.78	2.97	138.15	0.00437	67.97	0.9870	–14.13
600	0.9305	–46.2	2.90	130.12	0.00483	64.86	0.9847	–16.87
700	0.9105	–53.33	2.81	122.26	0.0051	62.13	0.9832	–19.61
800	0.8911	–60.2	2.73	114.65	0.0052	59.88	0.9817	–22.35
900	0.8723	–67.03	2.65	107.2	0.00515	58.8	0.9796	–25.03
1000	0.8521	–73.74	2.56	99.78	0.00498	58.03	0.9785	–27.08

8.2 Noise data for amplifier A

Table 10. Noise data for amplifier A

$V_{DS(A)}$ = 5 V; V_{G2-S} = 4 V; $I_{D(A)}$ = 19 mA, T_{amb} = 25 °C; typical values.

f (MHz)	NF_{min} (dB)	Γ_{opt}		r_n (ratio)
		(ratio)	(deg)	
400	0.9	0.749	23.7	0.667
800	1.2	0.688	48.65	0.583

8.3 Dynamic characteristics for amplifier B

Table 11. Dynamic characteristics for amplifier B

Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; $V_{DS(B)}$ = 5 V; $I_{D(B)}$ = 13 mA.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$\|y_{fs}\|$	forward transfer admittance	T_j = 25 °C		28	33	43	mS
$C_{iss(G1)}$	input capacitance at gate1	f = 100 MHz	[1]	-	1.9	2.4	pF
$C_{iss(G2)}$	input capacitance at gate2	f = 100 MHz	[1]	-	3.4	-	pF
C_{oss}	output capacitance	f = 100 MHz	[1]	-	0.85	-	pF
C_{rss}	reverse transfer capacitance	f = 100 MHz	[1]	-	20	-	fF
G_{tr}	transducer power gain	$B_S = B_{S(opt)}$; $B_L = B_{L(opt)}$	[1]				
		f = 200 MHz; G_S = 2 mS; G_L = 0.5 mS		32	36	40	dB
		f = 400 MHz; G_S = 2 mS; G_L = 1 mS		29	33	37	dB
		f = 800 MHz; G_S = 3.3 mS; G_L = 1 mS		27	31	35	dB
NF	noise figure	f = 11 MHz; G_S = 20 mS; B_S = 0 S		-	4	-	dB
		f = 400 MHz; $Y_S = Y_{S(opt)}$		-	0.9	1.5	dB
		f = 800 MHz; $Y_S = Y_{S(opt)}$		-	1.2	1.9	dB

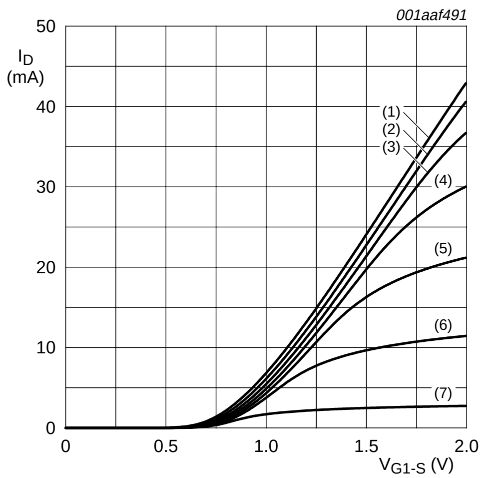
Table 11. Dynamic characteristics for amplifier B *…continued*
Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; $V_{DS(B)}$ = 5 V; $I_{D(B)}$ = 13 mA.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Xmod	cross modulation	input level for k = 1 %; f_w = 50 MHz; f_{unw} = 60 MHz	[2]				
		at 0 dB AGC		90	-	-	dBµV
		at 10 dB AGC		-	88	-	dBµV
		at 20 dB AGC		-	94	-	dBµV
		at 40 dB AGC		100	103	-	dBµV

[1] Calculated from S-parameters.

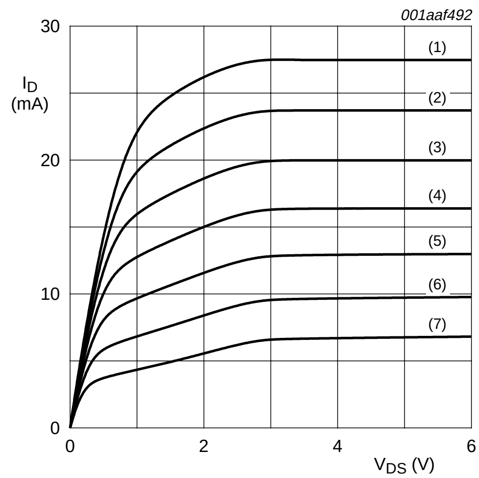
[2] Measured in Figure 32 test circuit.

8.3.1 Graphs for amplifier B



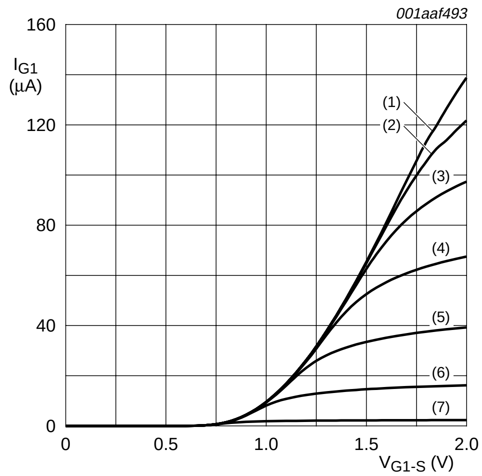
(1) V_{G2-S} = 4 V.
(2) V_{G2-S} = 3.5 V.
(3) V_{G2-S} = 3 V.
(4) V_{G2-S} = 2.5 V.
(5) V_{G2-S} = 2 V.
(6) V_{G2-S} = 1.5 V.
(7) V_{G2-S} = 1 V.
$V_{DS(B)}$ = 5 V; T_j = 25 °C.

Fig 17. Amplifier B: transfer characteristics; typical values



(1) $V_{G1-S(B)}$ = 1.6 V.
(2) $V_{G1-S(B)}$ = 1.5 V.
(3) $V_{G1-S(B)}$ = 1.4 V.
(4) $V_{G1-S(B)}$ = 1.3 V.
(5) $V_{G1-S(B)}$ = 1.2 V.
(6) $V_{G1-S(B)}$ = 1.1 V.
(7) $V_{G1-S(B)}$ = 1.0 V.
V_{G2-S} = 4 V; T_j = 25 °C.

Fig 18. Amplifier B: output characteristics; typical values



(1) V_{G2-S} = 4 V.

(2) V_{G2-S} = 3.5 V.

(3) V_{G2-S} = 3 V.

(4) V_{G2-S} = 2.5 V.

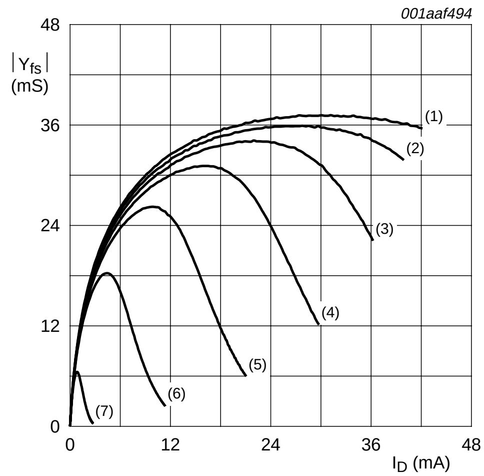
(5) V_{G2-S} = 2 V.

(6) V_{G2-S} = 1.5 V.

(7) V_{G2-S} = 1 V.

$V_{DS(B)}$ = 5 V; T_j = 25 °C.

Fig 19. Amplifier B: gate1 current as a function of gate1 voltage; typical values



(1) V_{G2-S} = 4 V.

(2) V_{G2-S} = 3.5 V.

(3) V_{G2-S} = 3 V.

(4) V_{G2-S} = 2.5 V.

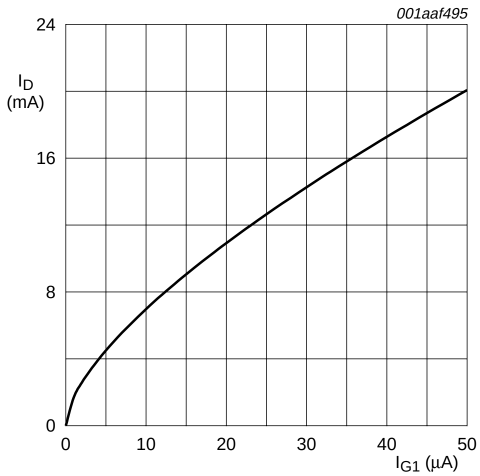
(5) V_{G2-S} = 2 V.

(6) V_{G2-S} = 1.5 V.

(7) V_{G2-S} = 1 V.

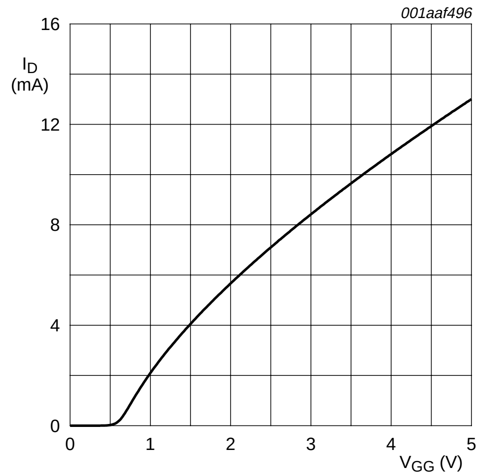
$V_{DS(B)}$ = 5 V; T_j = 25 °C.

Fig 20. Amplifier B: forward transfer admittance as a function of drain current; typical values



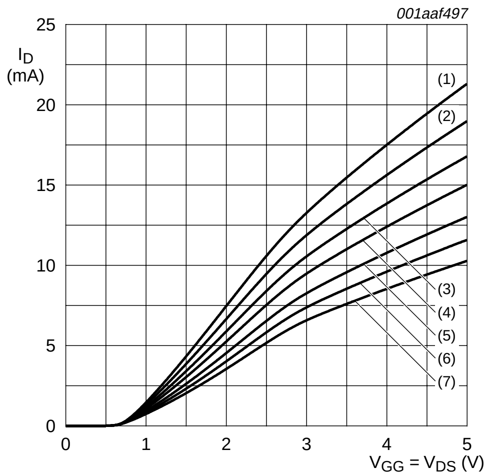
$V_{DS(B)}$ = 5 V; V_{G2-S} = 4 V; T_j = 25 °C.

Fig 21. Amplifier B: drain current as a function of gate1 current; typical values



$V_{DS(B)}$ = 5 V; V_{G2-S} = 4 V; $R_{G1(B)}$ = 150 kΩ; T_j = 25 °C.

Fig 22. Amplifier B: drain voltage as a function of gate1 supply voltage (V_{GG}); typical values



(1) $R_{G1(B)}$ = 68 kΩ.

(2) $R_{G1(B)}$ = 82 kΩ.

(3) $R_{G1(B)}$ = 100 kΩ.

(4) $R_{G1(B)}$ = 120 kΩ.

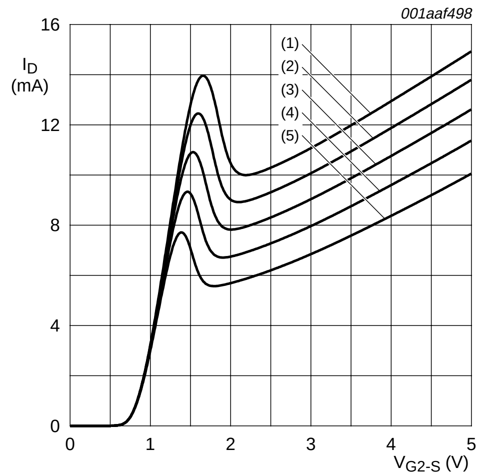
(5) $R_{G1(B)}$ = 150 kΩ.

(6) $R_{G1(B)}$ = 180 kΩ.

(7) $R_{G1(B)}$ = 220 kΩ.

$V_{G2\text{-}S}$ = 5 V; $R_{G1(B)}$ connected to V_{GG}; T_j = 25 °C.

Fig 23. Amplifier B: drain current as a function of V_{DS} and V_{GG}; typical values



(1) V_{GG} = 5.0 V.

(2) V_{GG} = 4.5 V.

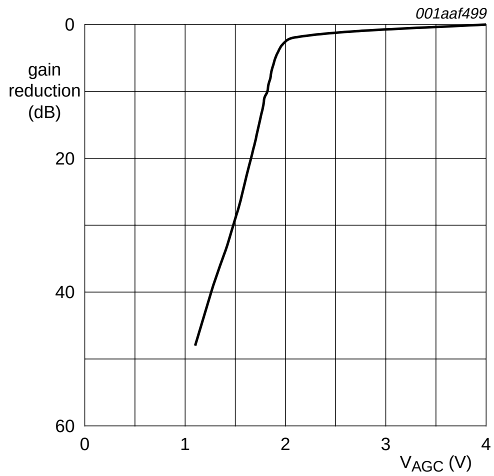
(3) V_{GG} = 4.0 V.

(4) V_{GG} = 3.5 V.

(5) V_{GG} = 3.0 V.

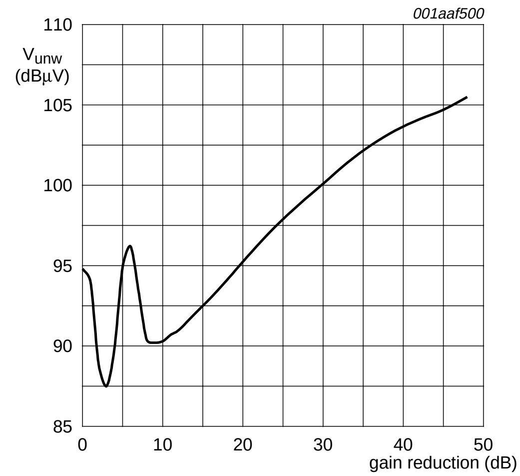
$R_{G1(B)}$ = 150 kΩ; T_j = 25 °C.

Fig 24. Amplifier B: drain current as a function of gate2 voltage; typical values



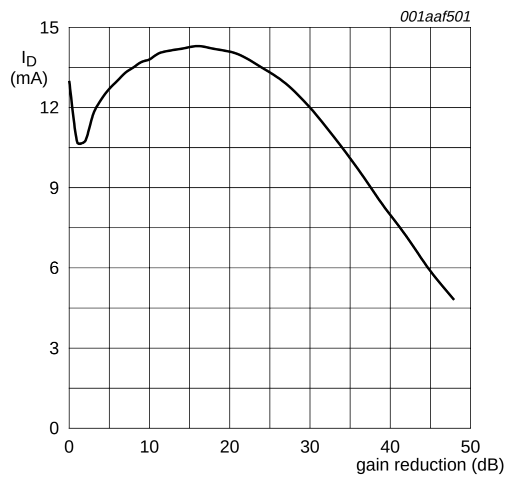
$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S(nom)}$ = 4 V; $R_{G1(B)}$ = 150 kΩ; $I_{D(nom)(B)}$ = 13 mA; T_{amb} = 25 °C; see Figure 32.

Fig 25. Amplifier B: typical gain reduction as a function of the AGC voltage; typical values



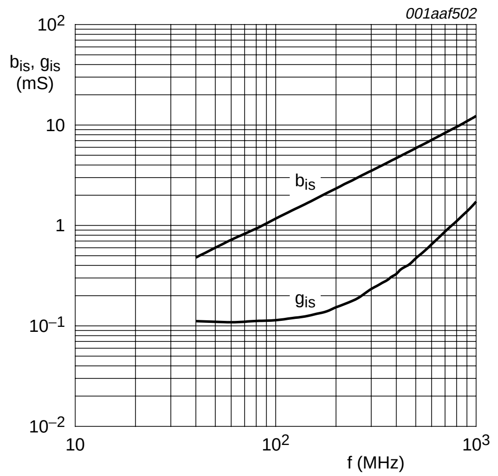
$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S(nom)}$ = 4 V; $R_{G1(B)}$ = 150 kΩ; $I_{D(nom)(B)}$ = 13 mA; f_w = 50 MHz; f_{unw} = 60 MHz; T_{amb} = 25 °C; see Figure 32.

Fig 26. Amplifier B: unwanted voltage for 1 % cross modulation as a function of gain reduction; typical values



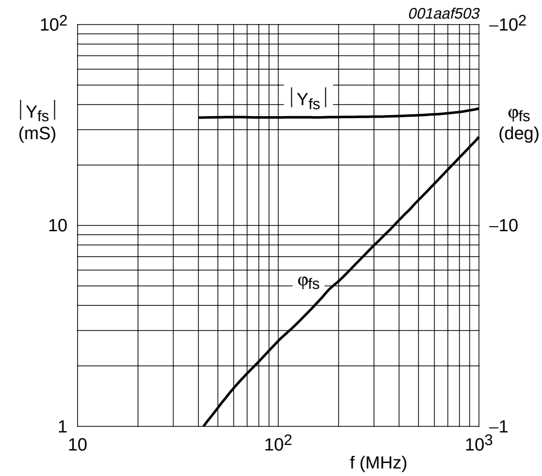
$V_{DS(B)}$ = V_{GG} = 5 V; $V_{G2\text{-}S(nom)}$ = 4 V; $R_{G1(B)}$ = 150 kΩ; $I_{D(nom)(B)}$ = 13 mA; f = 50 MHz; T_{amb} = 25 °C; see Figure 32.

Fig 27. Amplifier B: typical drain current as a function of gain reduction; typical values



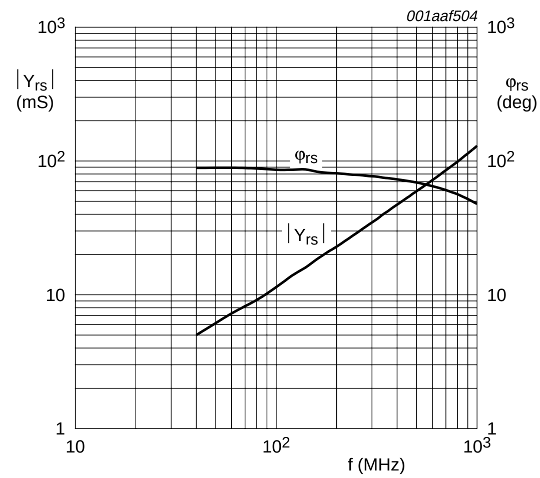
$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(A)}$ = 0 V;
$I_{D(B)}$ = 13 mA.

Fig 28. Amplifier B: input admittance as a function of frequency; typical values



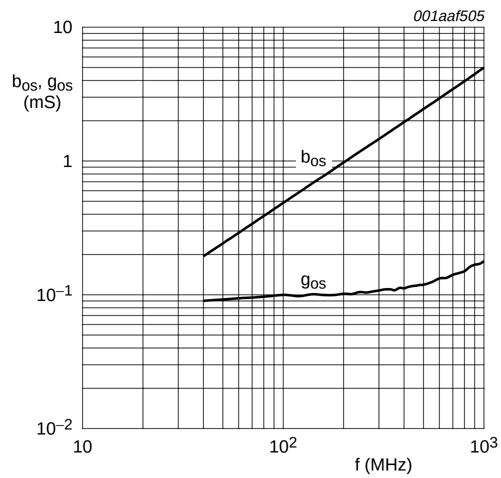
$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(A)}$ = 0 V;
$I_{D(B)}$ = 13 mA.

Fig 29. Amplifier B: forward transfer admittance and phase as a function of frequency; typical values



$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(A)}$ = 0 V;
$I_{D(B)}$ = 13 mA.

Fig 30. Amplifier B: reverse transfer admittance and phase as a function of frequency; typical values



$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $V_{DS(A)}$ = 0 V;
$I_{D(B)}$ = 13 mA.

Fig 31. Amplifier B: output admittance as a function of frequency; typical values

8.3.2 Scattering parameters for amplifier B

Table 12. Scattering parameters for amplifier B

$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $I_{D(B)}$ = 13 mA; $V_{DS(A)}$ = 0 V; $V_{G1\text{-}S(A)}$ = 0 V; T_{amb} = 25 °C; typical values.

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)	Magnitude (ratio)	Angle (deg)
40	0.9874	–2.79	3.41	177.08	0.00054	89.27	0.992	–1.26
100	0.9883	–6.8	3.41	172.57	0.00113	90.81	0.9900	–2.91
200	0.9844	–13.52	3.39	165.23	0.00224	89.67	0.9897	–5.81
300	0.9777	–20.2	3.36	157.88	0.00336	89.02	0.9889	–8.7
400	0.9684	–26.83	3.32	150.6	0.00447	88.43	0.9881	–11.61
500	0.9578	–33.32	3.27	143.38	0.0055	87.64	0.9870	–14.52
600	0.9442	–39.8	3.21	136.22	0.00649	87.53	0.9851	–17.39
700	0.9291	–46.08	3.16	129.15	0.00741	87.51	0.9838	–20.3
800	0.9147	–52.18	3.08	122.25	0.00828	87.7	0.9825	–23.2
900	0.9002	–58.35	3.08	115.4	0.00914	88.14	0.9803	–26.06
1000	0.8836	–64.49	2.93	108.49	0.00997	88.26	0.9789	–29.03

8.4 Noise data for amplifier B

Table 13. Noise data for amplifier B

$V_{DS(B)}$ = 5 V; $V_{G2\text{-}S}$ = 4 V; $I_{D(B)}$ = 13 mA, T_{amb} = 25 °C; typical values.

f (MHz)	NF_{min} (dB)	Γ_{opt}		r_n (ratio)
		(ratio)	(deg)	
400	0.9	0.743	20.27	0.65
800	1.2	0.687	42.08	0.581

9. Test information

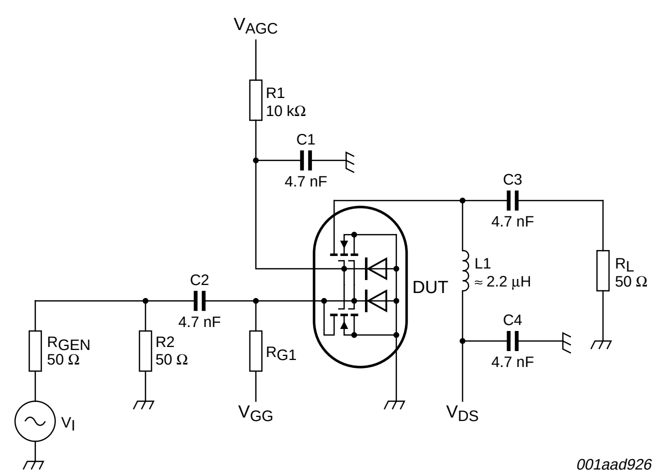
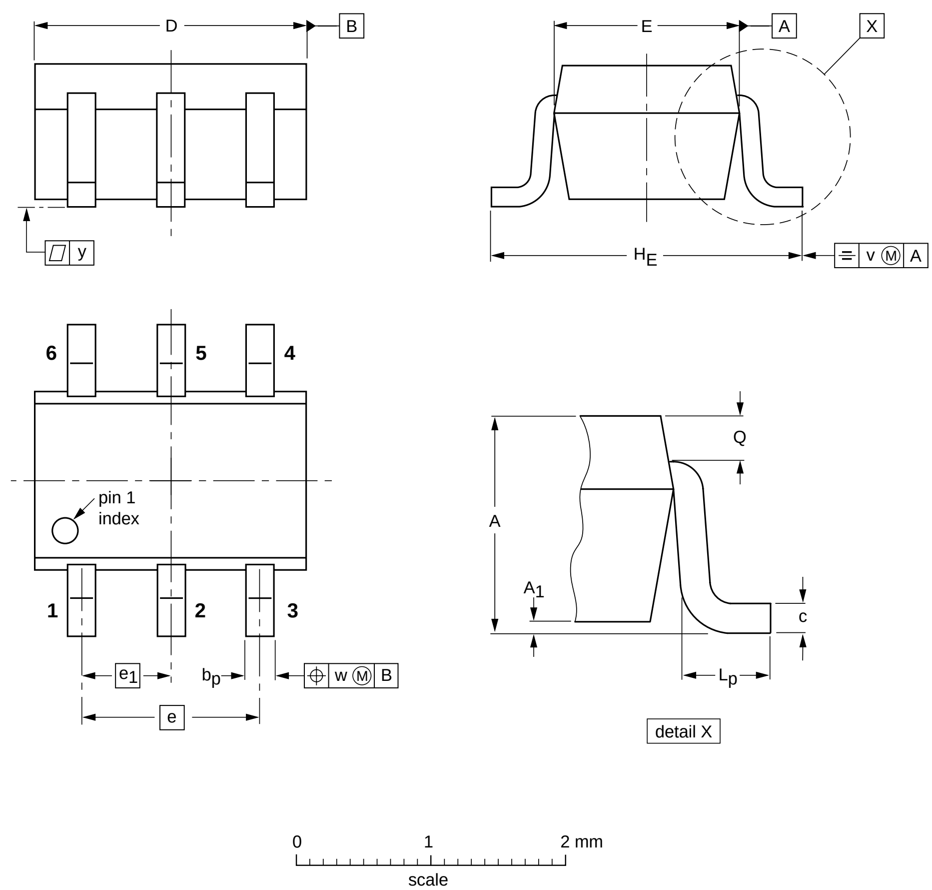


Fig 32. Cross modulation test setup (for one MOSFET)

10. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

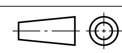
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 33. Package outline SOT363

11. Abbreviations

Table 14. Abbreviations

Acronym	Description
AGC	Automatic Gain Control
DC	Direct Current
MOSFET	Metal-Oxide-Semiconductor Field-Effect Transistor
UHF	Ultra High Frequency
VHF	Very High Frequency

12. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF1210_1	20061025	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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